Record Nr. UNINA9910299588803321 Autore Cheng Jie Titolo Research on Chemical Mechanical Polishing Mechanism of Novel Diffusion Barrier Ru for Cu Interconnect // by Jie Cheng Singapore:,: Springer Singapore:,: Imprint: Springer,, 2018 Pubbl/distr/stampa **ISBN** 981-10-6165-3 Edizione [1st ed. 2018.] 1 online resource (XVIII, 137 p. 103 illus.) Descrizione fisica Springer Theses, Recognizing Outstanding Ph.D. Research, , 2190-Collana 5053 621.38152 Disciplina Soggetti Manufactures Tribology Corrosion and anti-corrosives Coatings Electronics Microelectronics Manufacturing, Machines, Tools, Processes Tribology, Corrosion and Coatings Electronics and Microelectronics, Instrumentation Lingua di pubblicazione Inglese **Formato** Materiale a stampa Livello bibliografico Monografia Nota di bibliografia Includes bibliographical references. Sommario/riassunto This thesis addresses selected unsolved problems in the chemical mechanical polishing process (CMP) for integrated circuits using ruthenium (Ru) as a novel barrier layer material. Pursuing a systematic approach to resolve the remaining critical issues in the CMP, it first investigates the tribocorrosion properties and the material removal mechanisms of copper (Cu) and Ru in KIO4-based slurry. The thesis subsequently studies Cu/Ru galvanic corrosion from a new micro and

in-situ perspective, and on this basis, seeks ways to mitigate corrosion using different slurry additives. The findings presented here constitute a significant advance in fundamental and technical investigations into

the CMP, while also laying the groundwork for future research.